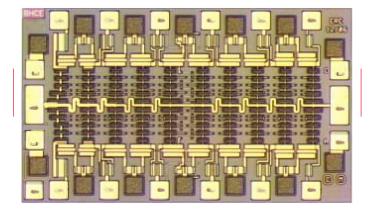
Keysight 1GC1-4094 DC - 26.5 GHz Biasable Integrated Diode Limiter

Data Sheet



Features

- DC to 26.5 GHz limiter
- Can be biased for adjustable limit level
- Low distortion

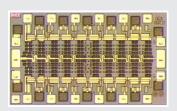


Description

The 1GC1-4094 is a 26.5 GHz integrated diode limiter that can be used to protect sensitive RF circuits from excess RF power, DC transients, and ESD.

The 1GC1-4094 can be used as an unbiased 23 dBm passive limiter; it also provides adjustable limiting and peak power detection capabilities.

The 1GC1-4094 is fabricated using Keysight Technologies, Inc. GaAs HBT process.



- Chip size: $1,440 \times 870 \mu m$ (56.7 × 34.2 mils)
- Chip size tolerance: $\pm 10 \ \mu m$ ($\pm 0.4 \ mils$)
- Chip thickness: 127 \pm 15 μm (5.0 \pm 0.6 mils)
- Pad dimensions: $80\times80~\mu m$ (3.2 \times 3.2 mils) DC $80\times160~\mu m$ (3.2 \times 6.3 mils) RF

Absolute maximum ratings^{1 2}

Symbol	Parameters/conditions		Min	Max	Units
P_{in}	Continuous incident power at RF_{IN} RL at RF_{IN} = 10 dB	RL at RF _{OUT} > 10 dB		30	dBm
		RL at RF _{OUT} > 15 dB		33	dBm
	Continuous incident power at RF _{OUT} RF at RF _{IN} = 0 dB	RL at RF _{OUT} > 10 dB		25	dBm
		RL at RF _{OUT} > 15 dB		28	dBm
Vanode	Bias on anode ads		-15	0	dBm
V _{cathode}	Bias on cathode pads		0	15	V
_l _{in}	DC current into ${\rm RF_{IN}}$ or ${\rm RF_{OUT}}$ pads			288	V
T _{bs}	Maximum backside temperature			85	mA
T _i	Diode junction temperature			170	°C
T _{max}	Maximum assembly temperature ³			300	°C
T _{stg}	Storage temperature		-65	165	°C

^{1.} Operation in excess of any one of these conditions may result in permanent damage to this device. If you need to operate higher, please contact your local Keysight sales office.

^{2.} Calculated using backside (ambient) temperature of 85 °C, unless otherwise noted.

^{3.} Sixty-second maximum.

DC specifications/physical properties¹

Symbol	Parameters/conditions	Min	Тур	Max	Units
Vfwd_A, Vfwd_B	Diode forward voltage at 1.0 mA, anode or cathode pads to ${\rm RF}_{_{\rm IN}}$	2.5	2.8	3.5	V
Rfwd_A, Rfwd_B	Diode forward voltage at 1.0 mA, anode or cathode pads to ${\rm RF}_{_{\rm IN}}$		8	15	Ω
Irev_A Irev_B	Reverse current in bias network, anode or cathode pads to ${\rm RF}_{\scriptscriptstyle \rm IN}$	2.5	3	3.5	mA
Rseries	Through series resistance (RF _{IN} to RF _{OUT})		2.4	7	Ω
Rsense	Sense Resistor	8	10	12.5	kΩ
V_RF _{IN}	Vanode = -15 V, Vcathode = +15 V	-0.1	0	0.1	V

^{1.} Measured on wafer with T_{chuck} = 25 °C.

RF specifications¹

Symbol	Parameters/conditions		Min.	Тур.	Max.	Units	
		10 GHz		-28	-18		
S ₁₁ , S ₂₂	Reflection	20 GHz		-16	-10	dB	
		26.5 GHz		-16	-9	-	
S ₂₁ , S ₁₂		10 GHz	-1	-0.7			
	Through gain	20 GHz	-2	-1.3		dB	
		26.5 GHz	-2.7	-1.8		-	
Δau d	Group delay flatness	40 GHz		±1.0		pS	
P _{-1 dB}	1 dB gain compression	Vanode = 0, Vcathode = 0		23		- dBm -	
		Vanode = -10 V, Vcathode = 10		32			
		Vanode = -10 V, Vcathode = 10		Voltage variable			
SHI	Second harmonic intercept $f_o = 10 \text{ GHz}$	Vanode = Vcathode = 0		84		- dBm	
		Vanode = -10 V, Vcathode = 10		101			
ТШІ	Third harmonic intercept f _o = 10 GHz	Vanode = Vcathode = 0		36		- dBm	
THI		Vanode = -10 V, Vcathode = 10		52			
TOI	Third order intercept $f_o = 10 \text{ GHz}$, $\Delta f = 100 \text{ kHz}$	Vanode = 0 V, Vcathode = 0V 36		36			
		Vanode = -6.5 V, Vcathode = 6.5 V		47		– dBm –	
		Vanode = -10 V, Vcathode = 10V		50			
		Vanode = -15 V, Vcathode = 15V		55			

^{1.} Measured on wafer with $T_{chuck} = 25 \, ^{\circ}C$.

ED specifications¹

Symbol	Parameters/conditions		Min.	Тур.	Max.	Units
		${\rm RF_{IN}}$ and ${\rm RF_{OUT}}$ pads, anode $\&$ cathode grounded		15,000		
ESD	ESD No Damage Level	Any pad with all other pads open		500		V
		Any pad with another pad shorted to Gnd		200		

^{1.} Using human body model as ESD generator. circuit equivalent is 100 pF, 1500 Ω .

Applications

The 1GC1-4094 can be used as a protection circuit for ESD and DC transients, as a Reverse Power Protection (RPP) device, or as an adjustable RF limiter.

Typical applications include receiver and source protection from overpower and ESD. RF_{OUT} is connected to the device that needs protection.

Biasing

Vanode can be biased from 0V to -15 V and Vcathode can be biased from 0 V to + 15 V. Typically the magnitude of these two biases are made equal so that the DC voltage on the RF_{IN} and RF_{OUT} pads is 0 V. A typical assembly drawing is shown in Fig. 10 with caps mounted close to the chip for the bias lines. It is important that the bias lines provide a low impedance to ground close to the chip for maximum ESD protection.

Operation

The 1GC1-4094 functions as a limiter with the limiting level set by the bias at Vanode and Vcathode. It will also protect against electrical transisents and ESD.

RoHS Compliance

This device is RoHS Compliant. This means the component meets the requirements of the European Parliament and the Council of the European Union Restriction of Hazardous Substances Directive 2011/65/EU, commonly known as RoHS. The six regulated substances are lead, mercury, cadmium, chromium VI (hexavalent), polybrominated biphenyls (PBB) and polybrominated biphenyl ethers (PBDE). RoHS compliance implies that any residual concentration of these substances is below the RoHS Directive's maximum concentration values (MVC); being less than 1000 ppm by weight for all substances except for cadmium which is less than 100 ppm by weight.

Assembly Techniques

See Figure 11 for bond pad locations. Epoxy die-attach using a conductive epoxy or solder die-attach using a fluxless gold-tin nsolder preform. Gold wire bonds or mesh bonds (500-line/inch or equivalent) should be used at the RF_{IN} and RF_{OUT} pads. The RF_{IN} and RF_{OUT} pads can accommodate double wire bonds. The 1GC1-4094 is designed to have better return loss with a small inductance at the RF_{IN} and RF_{OUT} pads; a single bond wire about 10 mils long is best. For long bond wires, double bond wires are recommended.

Properly assembled, the 1GC1-4094 is very ESD rugged when zapped at the RF $_{\rm IN}$ and RF $_{\rm OUT}$ Pads, However, during assembly and handling, the device requires all ESD precautions since an ESD zap of more than 200 V can damage the device.

The Keysight Technologies, Inc. *GaAs MMIC ESD, Die Attach and Bonding Guidelines - Application Note* (5991-3484EN) provides basic information on these subjects.

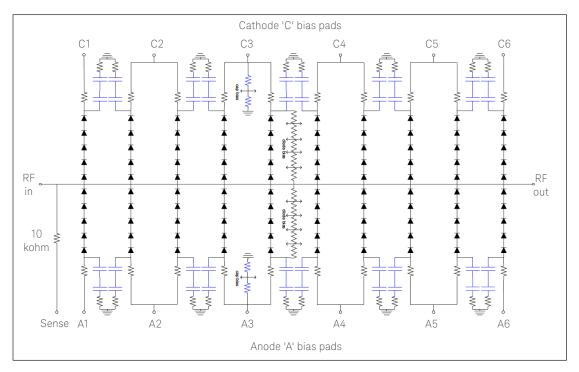


Figure 1. 1GC1-4094 functional topologies

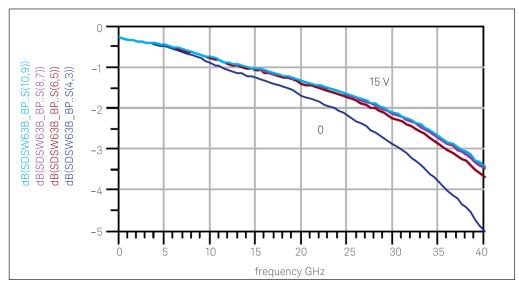


Figure 2. 1GC1-4094 insertion loss bias = 0 V, \pm 5 V, \pm 10 V, \pm 15 V

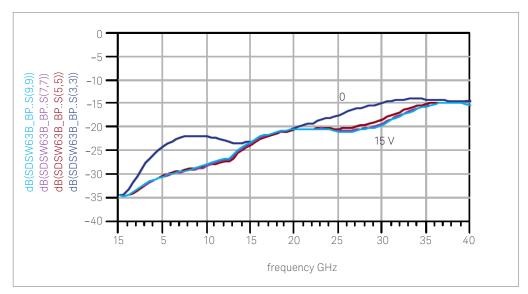


Figure 3. 1GC1-4094 input return loss bias = 0 V, \pm 5 V, \pm 10 V, \pm 15 V

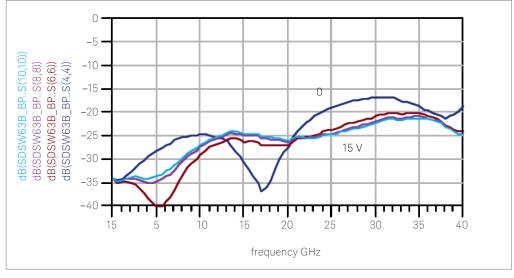


Figure 4. 1GC1-4094 output return loss bias = 0 V, \pm 5 V, \pm 10 V, \pm 15 V

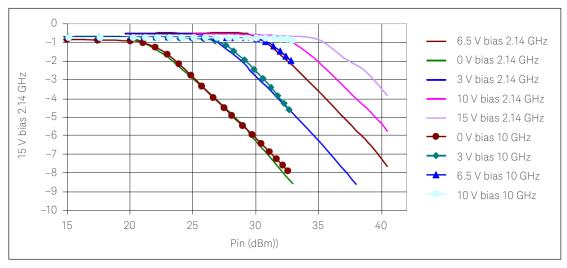


Figure 5. 1GC1-4094 gain vs pin vs bias (2.14 GHz and 10 GHz)

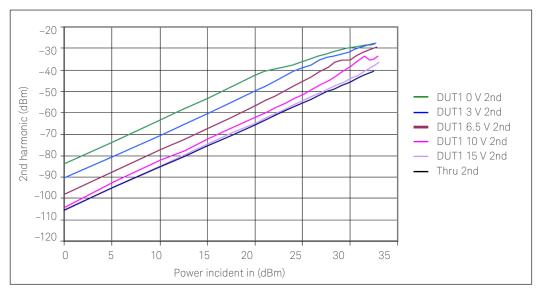


Figure 6. 1GC1-4094 2nd harmonic vs pin vs bias @ f_0 = 10 GHz

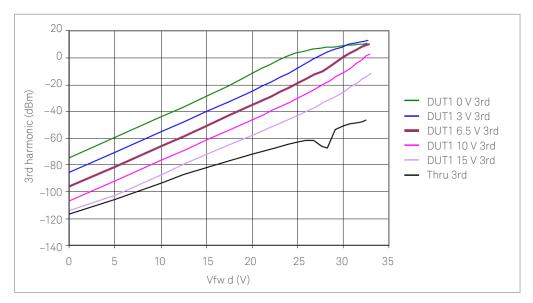


Figure 7. 1GC1-4094 3rd harmonic vs pin vs bias @ $f_{\rm o}$ = 10 GHz

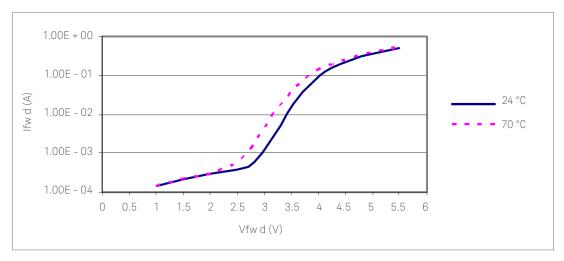


Figure 8. I-V center conductor (RF_{in}) to anode or cathode bias

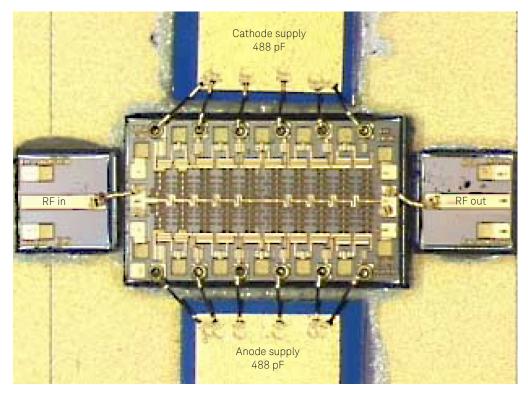


Figure 10. 1GC1-4094 sample bonding & assembly

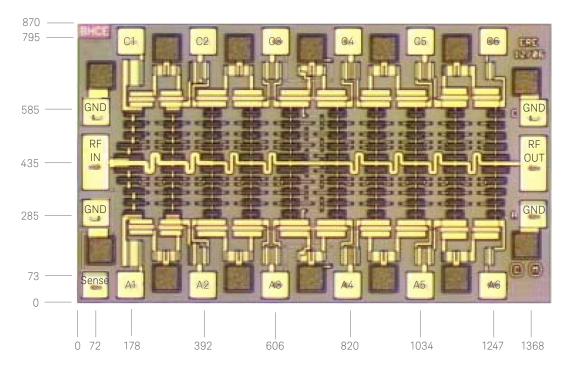
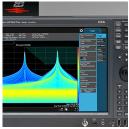


Figure 11. 1GC1-4094 bonding pad locations

Evolving

Our unique combination of hardware, software, support, and people can help you reach your next breakthrough. We are unlocking the future of technology.







From Hewlett-Packard to Agilent to Keysight

myKeysight

myKeysight

www.keysight.com/find/mykeysight

A personalized view into the information most relevant to you.

KEYSIGHT SERVICES Accelerate Technology Adoption. Lower costs.

Keysight Services

www.keysight.com/find/service

Keysight Services can help from acquisition to renewal across your instrument's lifecycle. Our comprehensive service offerings—one-stop calibration, repair, asset management, technology refresh, consulting, training and more—helps you improve product quality and lower costs.

Keysight Channel Partners

www.keysight.com/find/channelpartners

Get the best of both worlds: Keysight's measurement expertise and product breadth, combined with channel partner convenience.

This data sheet contains a variety of typical and guaranteed performance data. The information supplied should not be interpreted as a complete list of circuit specifications. Customers considering the use of this, or other Keysight Technologies GaAs ICs, for their design should obtain the current production specifications from Keysight. In this data sheet the term typical refers to the 50th percentile performance. For additional information contact Keysight at MMIC_Helpline@keysight.com.

The product described in this data sheet is RoHS Compliant. See RoHS Compliance section for more details.

www.keysight.com/find/mmic

For more information on Keysight Technologies' products, applications or services, please contact your local Keysight office. The complete list is available at: www.keysight.com/find/contactus

Americas

Canada	(877) 894 4414
Brazil	55 11 3351 7010
Mexico	001 800 254 2440
United States	(800) 829 4444

Asia Pacific

Australia	1 800 629 485
China	800 810 0189
Hong Kong	800 938 693
India	1 800 11 2626
Japan	0120 (421) 345
Korea	080 769 0800
Malaysia	1 800 888 848
Singapore	1 800 375 8100
Taiwan	0800 047 866
Other AP Countries	(65) 6375 8100

Europe & Middle East

Austria	0800 001122
Belgium	0800 58580
Finland	0800 523252
France	0805 980333
Germany	0800 6270999
Ireland	1800 832700
Israel	1 809 343051
Italy	800 599100
Luxembourg	+32 800 58580
Netherlands	0800 0233200
Russia	8800 5009286
Spain	800 000154
Sweden	0200 882255
Switzerland	0800 805353
	Opt. 1 (DE)
	Opt. 2 (FR)

For other unlisted countries: www.keysight.com/find/contactus (BP-06-08-16)

Opt. 3 (IT)

0800 0260637



United Kingdom

www.keysight.com/go/quality Keysight Technologies, Inc. DEKRA Certified ISO 9001:2015 Quality Management System

